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#6/Brandt B
PATENTS
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Noriaki Oda, et al.

Examiner: Monica Lewis

Serial No: 09/863,737

Art Unit: 2822

Filed: May 23, 2001

Docket: 12562A

For: SEMICONDUCTOR DEVICE AND
METHOD FOR MANUFACTURING
THE SAME

Dated: May 15, 2002

Assistant Commissioner for Patents
Washington, D.C. 20231

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RESPONSE

Sir:

In response to the Office Action dated January 15, 2002, applicants submit the following Amendment for entry in the above-identified application.

IN THE SPECIFICATION:

Please amend the specification as follows:

Replace the paragraph that begins on Page 2, line 28 with the following:

B
Subsequently, as shown in Fig. 1, a third interlayer insulating film 17 having a viahole 18 is formed, a tungsten plug 19 is formed in the viahole 18, and a barrier metal layer 5C, an aluminum layer 6C and a titanium nitride layer 7C are successively formed. Thereafter, a desired pattern is left to form the third layer wiring 20. Then, a cover film 21 is formed, thereby completing the final structure shown in Fig. 1.

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on May 15, 2002.

Dated: May 15, 2002

Lisa Fiumara